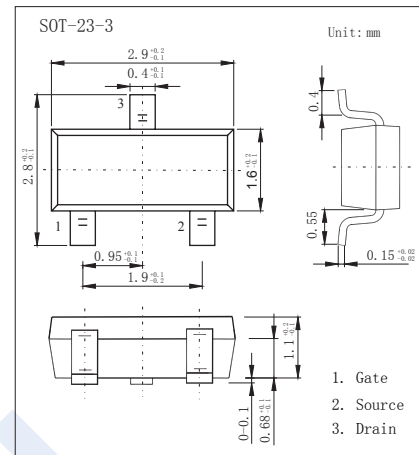
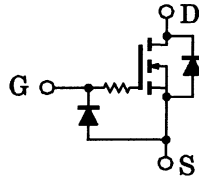


N-Channel MOSFET

2SK2033

■ Features

- $V_{DS} (V) = 20V$
- $I_D = 100mA$
- $R_{DS(ON)} < 12 \Omega$ ($V_{GS} = 2.5V$)
- Low threshold voltage: $V_{th} = 0.5 \sim 1.5 V$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 10	
Continuous Drain Current	I_D	100	mA
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

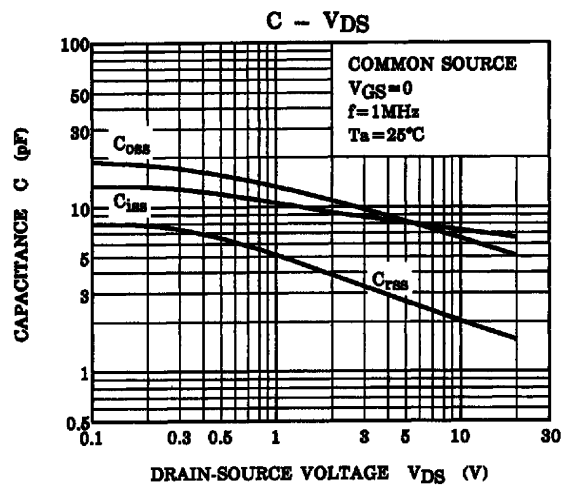
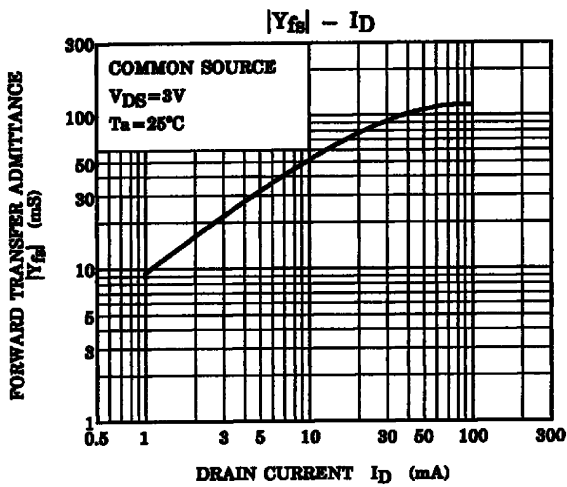
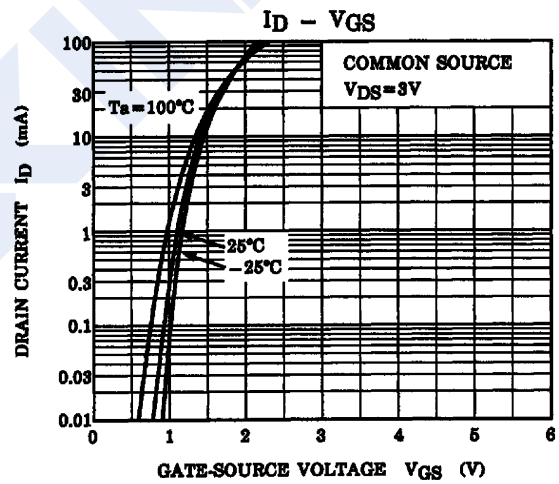
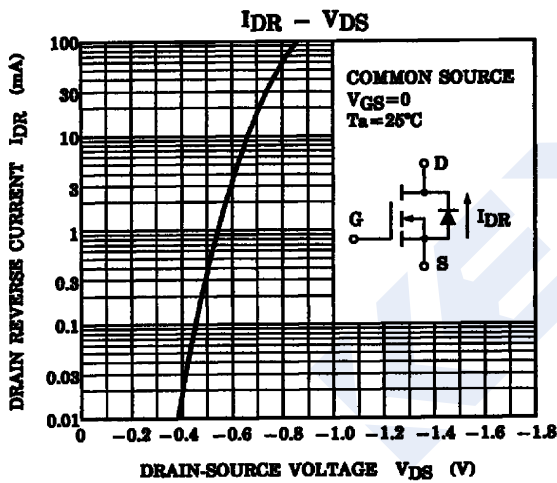
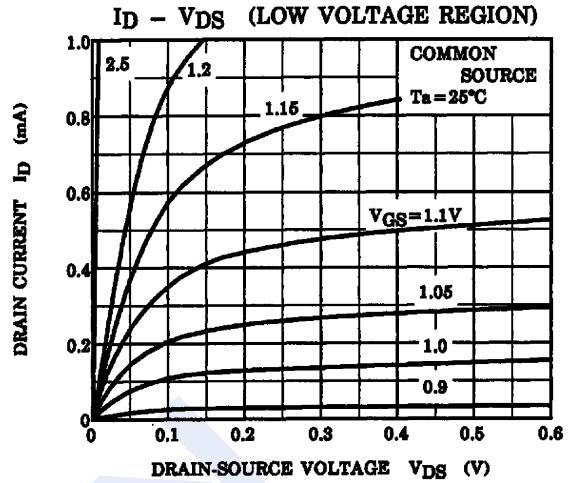
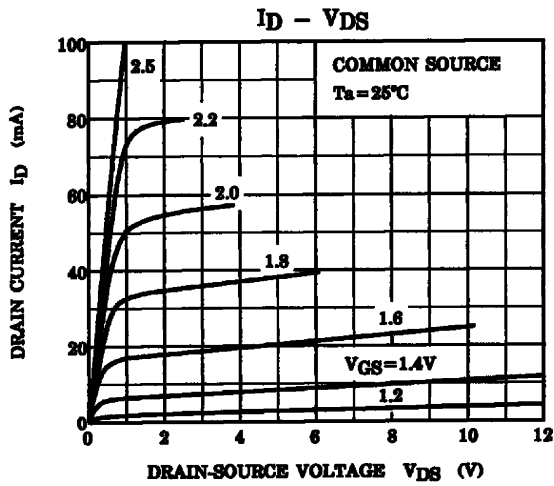
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = 250 \mu A, V_{GS} = 0V$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 10V$			± 1	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 3V, I_D = 100 \mu A$	0.5		1.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 2.5V, I_D = 10mA$			12	Ω
Forward Transconductance	g_{FS}	$V_{DS} = 3V, I_D = 10mA$	25	50		ms
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 3V, f = 1MHz$		8.5		μF
Output Capacitance	C_{oss}			3.3		
Reverse Transfer Capacitance	C_{rss}			9.3		
Turn-On DelayTime	$t_{d(on)}$	$V_{GS} = 0 \sim 2.5V, V_{DS} = 3V, I_D = 10mA$		160		ns
Turn-Off DelayTime	$t_{d(off)}$			150		

■ Marking

Marking	KP
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N-Channel MOSFET 2SK2033

■ Typical Characteristics



N-Channel MOSFET 2SK2033

■ Typical Characteristics

